

Abstracts

4-8 GHz Miniaturized GaAs FET Amplifier

S. Yamamura, N. Hidaka, Y. Tokumitsu and M. Fukuta. "4-8 GHz Miniaturized GaAs FET Amplifier." 1979 MTT-S International Microwave Symposium Digest 79.1 (1979 [MWSYM]): 335-337.

A 4-8 GHz GaAs FET balanced amplifier has been constructed on a 4mm x 5mm sapphire substrate. Lumped elements used in microwave- and DC bias-circuits, and 3-dB coupler were fabricated on the substrate using thin film technology.

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